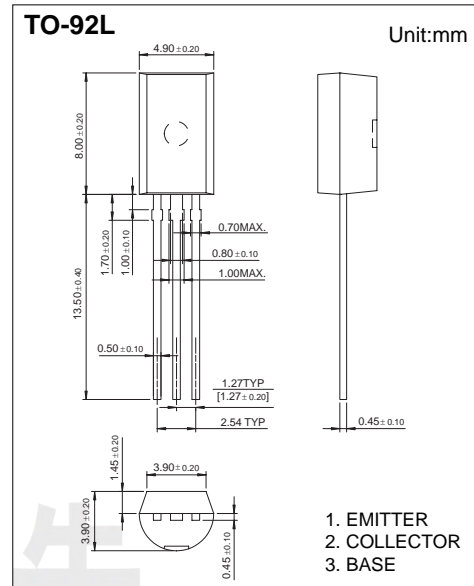


NPN Transistors 2SC2655

■ Features

- High Speed Switching Time
- Low saturation voltage
- Complementary to 2SA1020



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	VCBO	50	V
Collector - Emitter Voltage	VCEO	50	
Emitter - Base Voltage	VEBO	2	
Collector Current - Continuous	Ic	2	A
Collector Power Dissipation	Pc	0.9	W
Junction Temperature	TJ	150	°C
Storage Temperature	Tstg	-55 to 150	

Transistor

NPN Transistors 2SC2655

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V _{CB0}	I _c = 100 μA, I _E =0	50			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = 10 mA, I _B =0	50			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _c =0	5			
Collector cut-off current	I _{cBO}	V _{CB} = 50 V, I _E =0			1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _c =0			1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =1 A, I _B =50 mA			0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =1 A, I _B =50 mA			1.2	
DC current gain	h _{FE(1)}	V _{CE} = 2V, I _c = 500mA	70		240	
	h _{FE(2)}	V _{CE} = 2V, I _c = 1.5 A	40			
Tune on time	t _{on}	V _{CC} =30V, I _c =1A, I _{B1} =-I _{B2} =0.05A		0.15		μs
Storage time	t _{stg}			2		
Fall time	t _f			0.15		
Output capacitace	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		30		pF
Transition frequency	f _T	V _{CE} = 2V, I _c = 500mA		100		MHz

■ Classification of hFE

Rank	O	Y
Range	70-140	120-240

NPN Transistors 2SC2655

■ Typical Characteristics

